

This listing of claims will replace all prior versions of claims in the application.

Claims 1-36 (cancelled).

Claim 37 (currently amended): A photoresist composition that comprises:

- (a) a photoacid generator compound; and
- (b) a tetrapolymer that is at least substantially free of aromatic groups and comprises a hydroxyadamantyl moiety, a polymerized norbornene group, and at least two distinct repeat units that each has a photoacid-labile group.

Claim 38 (previously presented): The photoresist composition of claim 37 wherein the polymer comprises a lactone group.

Claim 39 (previously presented): The photoresist composition of claim 37 wherein the polymer comprises polymerized acrylate groups that comprise one or more photoacid-labile moieties.

Claim 40 (previously presented): The photoresist composition of claim 37 wherein the polymer comprises one or more nitrile moieties.

Claim 42-44 (cancelled).

Claim 45 (previously presented): The photoresist composition of claim 37 wherein the polymer is completely free of aromatic groups.

Claim 46 (previously presented): A microelectronic wafer substrate having coated thereon a layer of the photoresist composition of claim 37.

Claim 47 (currently amended): A photoresist composition that comprises:

- (a) a photoacid generator compound; and
- (b) a tetrapolymer that is at least substantially free of aromatic groups and comprises a hydroxyadamantyl moiety, a polymerized norbornene group, and a lactone group.

Claim 48 (cancelled).

Claim 49 (previously presented): The photoresist composition of claim 47 wherein the polymer comprises polymerized acrylate groups that comprise one or more photoacid-labile moieties.

Claim 50 (previously presented): The photoresist composition of claim 47 wherein the polymer comprises one or more nitrile moieties.

Claim 51 (previously presented): The photoresist composition of claim 47 wherein the polymer is completely free of aromatic groups.

Claim 52 (previously presented): The photoresist composition of claim 47 wherein the tetrapolymer comprises at least two distinct polymerized norbornene repeat units.

Claim 53 (previously presented): The photoresist composition of claim 37 wherein the tetrapolymer comprises at least two distinct polymerized norbornene repeat units.

Claim 54 (new): A photoresist composition that comprises:

- (a) a photoacid generator compound; and
- (b) a polymer that is at least substantially free of aromatic groups and comprises a hydroxyadamantyl moiety, and at least two distinct polymerized norbornene groups.

Claim 55 (new): The photoresist composition of claim 54 wherein the polymer comprises polymerized acrylate groups that comprise one or more photoacid-labile moieties.